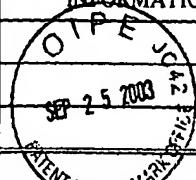


U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.	Serial No.			
				M-15230 US	10/632,154			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)				Applicant  Yi Ding				
APR 20 2004				Filing Date	Group			
				July 30, 2003	Unassigned 2823			
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*Examiner-Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
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	AG							
	AH							
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							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
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	AJ							
	AK							
	AL							
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KN	AN	United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other; And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.						
	AO							
	AP							
Examiner	<i>Khenneyan</i>	Date Considered	<i>07/23/04</i>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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KN	AR	Van Duuren, Michiel et al., "Compact poly-CMP Embedded Flash Memory Cells For One or Two Bit Storage," Philips Research Leuven, Kapeldreef 75, B3001 Leuven, Belgium, pages 73-74.
KN	AS	United States Patent Application No. 10/440,466, entitled "Fabrication Of Conductive Gates For Nonvolatile Memories From Layers With Protruding Portions," Filed on May 16, 2003; Attorney Docket No.: M-12979 US.
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KN	AU	United States Patent Application No. 10/440,508, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories Having Select, Floating And Control Gates," Filed on May 16, 2003; Attorney Docket No.: M-15204 US.

Examiner Kleinenguyen Date Considered 07/23/04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT  CPE SEP 25 2003 SEARCHED INDEXED MAILED CAT 2 RECEIVED U.S. PATENT & TRADEMARK OFFICE		Applicant	
(Use several sheets if necessary)		Yi Ding	
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KN	AZ	United States Patent Application No. 10/631,941, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate," Filed on July 30, 2003; Attorney Docket No.: M-15171 US.	
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KN	BB	United States Patent Application No. 10/632,007, entitled "Arrays Of Nonvolatile Memory Cells Wherin Each Cell Has Two Conductive Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15223 US.	
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KN	BD	United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US.	
KN	BE	United States Patent Application No. 10/632,186, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate And Having Upward Protrusions," Filed on July 30, 2003; Attorney Docket No.: M-15241 US.	
	BF		
	BG		
	BH		
Examiner <i>Yi Ding</i>	Date Considered	07/23/04	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant(s)	
		Yi Ding	
		Filing Date 07/30/03	Group
		Filed Herewith	
		<u>Unassigned</u> 2823	

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U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant(s)	
		Yi Ding	
		Filing Date <u>07/30/03</u>	Group
		Filed Herewith	Unassigned 2823

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R	BH	
	BI	
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